## DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

THYRISTOR-	BASED SRAM AI	ND METHOD FOR THE FAI	BRICATION T	HEREOF		
the specification of	which					
is attached hereto	o					
was filed on as Application Serial No and was amended on (if applicable).						
hereby state that I have reviewed and understand the contents of the above-identified specification including the claims, as amended by any amendment referred to above.						
before this invention not in public use capplication. I ackno	n thereof or more to or on sale in the U wledge the duty to	ame was ever known or used in han one year prior to this appl United States of America mor disclose information which is , Code of Federal Regulations,	ication, and that the than one year known to me to	at the same wa		
Section 365(b) of an any PCT internation listed below and have	ny foreign applicati nal application whic we also identified be	s under Title 35, United State on(s) for patent or inventor's ch designated at least one countries any foreign application for oplication on which priority is control of the state of the	ertificate, or Se y other than the patent or inven	ection 365(a) o e United States		
Prior Foreign App	lication(s):		Duii4 Cil			
Number	Country	Day/Month/Year filed	Priority Cla <u>Yes</u>	<u>No</u>		
I hereby claim the b below:	enefit under 35 USC	C 119(e) of any United States pr	ovisional appli	cation(s) listed		
Prior Provisional A	Application(s):					
Application Numb	er <u>Filing</u>	Date				
application(s), or Solisted below and, it disclosed in the printing paragraph of material information	ection 365(c) of any nsofar as the subjort United States or Fitle 35, United States in as defined in The filing date of the	e 35, United States Code, Sector PCT international application eet matter of each of the classification ates Code, Section 112, I acknowledge a prior application and the national application and the national sector is prior application and the na	designating the designating the ims of this application the manner provided the designations, Section 1.	e United States plication is no provided by the luty to disclosion 1.56 which		
Prior U.S. Applica	tion(s):					
Serial No.	Filing Date	Status: Patented, Pending,	Abandoned	_		

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru

Reg. No. 27,449

William D. Zahrt, II

Reg. No. 26,070

for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

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St. Sheet

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